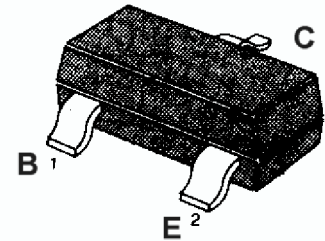


**APPLICATION:** High Current Applications.

**MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CBO</sub>	-30	V
Collector-emitter voltage	V <sub>CEO</sub>	-30	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-1500	mA
Collector Power Dissipation	P <sub>C</sub>	350	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C

**SOT-23**


1.Base 2 .Emitter 3 .Collector

**ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	100		430		V <sub>CE</sub> = -2V, I <sub>C</sub> = -500mA
Collector Cut-off Current	I <sub>CBO</sub>			-0.1	μA	V <sub>CB</sub> = -30V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			-0.1	μA	V <sub>EB</sub> = -5V, I <sub>C</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-30			V	I <sub>C</sub> = -1mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-30			V	I <sub>C</sub> = -10mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5			V	I <sub>E</sub> = -1mA, I <sub>C</sub> =0
Base-Emitte Voltage	V <sub>BE</sub>			-1	V	V <sub>CE</sub> = -2V, I <sub>C</sub> = -500mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			-2	V	I <sub>C</sub> = -1500mA, I <sub>B</sub> = -30mA
Gain bandwidth product	f <sub>T</sub>	30	50		MHz	I <sub>C</sub> = -500mA, V <sub>CE</sub> = -10V
Common Base Output Capacitance	C <sub>ob</sub>			30	PF	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f = 1MHz

**h<sub>FE</sub> Classification And Marking**

Print Mark	HO	HY	HG
Classification	O	Y	G
h <sub>FE</sub>	100~200	160~320	320~430